

PSMN015-60BS

N-channel 60 V 14.8 m Ω standard level MOSFET in D2PAK

Rev. 2 — 1 March 2012

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	60	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	50	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	86	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	23.7	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	12.6	14.8	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I_{D} = 25 A; V_{DS} = 30 V;	-	4.7	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15	-	20.9	-	nC
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 50 A; $V_{sup} \le 60$ V; R_{GS} = 50 Ω ; unclamped	-	-	44	mJ
		-				

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT404 (D2PAK)

[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN015-60BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Мах	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	60	V
drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	60	V
gate-source voltage		-20	20	V
drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	36	А
	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	50	А
peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see <u>Figure 3</u>	-	201	A
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	86	W
storage temperature		-55	175	°C
junction temperature		-55	175	°C
peak soldering temperature		-	260	°C
in diode				
source current	T _{mb} = 25 °C	-	50	А
peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	201	А
ruggedness				
non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 50 A; $V_{sup} \le 60$ V; R_{GS} = 50 Ω ; unclamped	-	44	mJ
	drain-source voltage drain-gate voltage gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature peak soldering temperature in diode source current peak source current ruggedness non-repetitive drain-source	$\begin{array}{ll} drain-source \ voltage & T_j \geq 25 \ ^\circ C; \ T_j \leq 175 \ ^\circ C \\ drain-gate \ voltage & T_j \geq 25 \ ^\circ C; \ T_j \leq 175 \ ^\circ C; \ R_{GS} = 20 \ k\Omega \\ gate-source \ voltage & & & \\ \\ drain \ current & V_{GS} = 10 \ V; \ T_{mb} = 100 \ ^\circ C; \ see \ Figure \ 1 \\ \hline V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ C; \ see \ Figure \ 1 \\ \hline v_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ C; \ see \ Figure \ 1 \\ \hline peak \ drain \ current & pulsed; \ t_p \leq 10 \ \mu s; \ T_{mb} = 25 \ ^\circ C; \ see \ Figure \ 2 \\ \hline storage \ temperature & \\ \hline peak \ soldering \ temperature & \\ \hline peak \ soldering \ temperature & \\ \hline peak \ soldering \ temperature & \\ \hline n \ diode & \\ \hline source \ current & T_{mb} = 25 \ ^\circ C \\ peak \ source \ current & T_{mb} = 25 \ ^\circ C \\ \hline peak \ source \ current & pulsed; \ t_p \leq 10 \ \mu s; \ T_{mb} = 25 \ ^\circ C \\ \hline ruggedness & \\ \hline non-repetitive \ drain-source & V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ ^\circ C; \ I_D = 50 \ A; \end{array}$	$\begin{array}{cccc} drain-source voltage & T_j \geq 25 \ ^{\circ}\text{C}; \ T_j \leq 175 \ ^{\circ}\text{C} & - \\ \\ drain-gate voltage & T_j \geq 25 \ ^{\circ}\text{C}; \ T_j \leq 175 \ ^{\circ}\text{C}; \ R_{GS} = 20 \ \text{k}\Omega & - \\ \\ gate-source voltage & -20 \\ \\ drain current & V_{GS} = 10 \ \text{V}; \ T_{mb} = 100 \ ^{\circ}\text{C}; \ see \ Figure 1 & - \\ \hline V_{GS} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ see \ Figure 1 & - \\ \hline V_{GS} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ see \ Figure 1 & - \\ \hline v_{GS} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ see \ Figure 2 & - \\ \\ storage temperature & T_{mb} = 25 \ ^{\circ}\text{C}; \ see \ Figure 2 & - \\ \hline storage temperature & -55 \\ \hline peak soldering temperature & -55 \\ peak soldering temperature & -55 \\ peak soldering temperature & -55 \\ \hline peak soldering temperature & -55 \\ \hline peak source current & T_{mb} = 25 \ ^{\circ}\text{C} & - \\ \hline peak source current & T_{mb} = 25 \ ^{\circ}\text{C} & - \\ \hline ruggedness & \\ \hline non-repetitive drain-source & V_{GS} = 10 \ \text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ I_D = 50 \ \text{A}; \ - \\ \end{array}$	$\label{eq:response} \begin{array}{ c c c } T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 175 \ ^{\circ}\text{C} & - & 60 \\ \hline \text{drain-gate voltage} & T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 175 \ ^{\circ}\text{C}; \ R_{GS} = 20 \ \text{k}\Omega & - & 60 \\ \hline \text{gate-source voltage} & -20 & 20 \\ \hline \text{drain current} & V_{GS} = 10 \ \text{V}; \ T_{mb} = 100 \ ^{\circ}\text{C}; \ \text{see Figure 1} & - & 36 \\ \hline V_{GS} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 1} & - & 50 \\ \hline \text{peak drain current} & \text{pulsed; } t_{p} \leq 10 \ \text{µs}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 2} & - & 86 \\ \hline \text{storage temperature} & -55 & 175 \\ \hline \text{junction temperature} & -55 & 175 \\ \hline \text{peak soldering temperature} & -55 & 175 \\ \hline \text{peak soldering temperature} & - & 260 \\ \hline \text{in diode} & & & \\ \hline \text{source current} & T_{mb} = 25 \ ^{\circ}\text{C} & - & 50 \\ \hline \text{peak source current} & T_{mb} = 25 \ ^{\circ}\text{C} & - & 50 \\ \hline \text{peak source current} & T_{mb} = 25 \ ^{\circ}\text{C} & - & 50 \\ \hline \text{peak source current} & T_{mb} = 25 \ ^{\circ}\text{C} & - & 50 \\ \hline \text{peak source current} & V_{GS} = 10 \ \text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ I_{D} = 50 \ \text{A}; & - & 44 \\ \hline \end{array}$

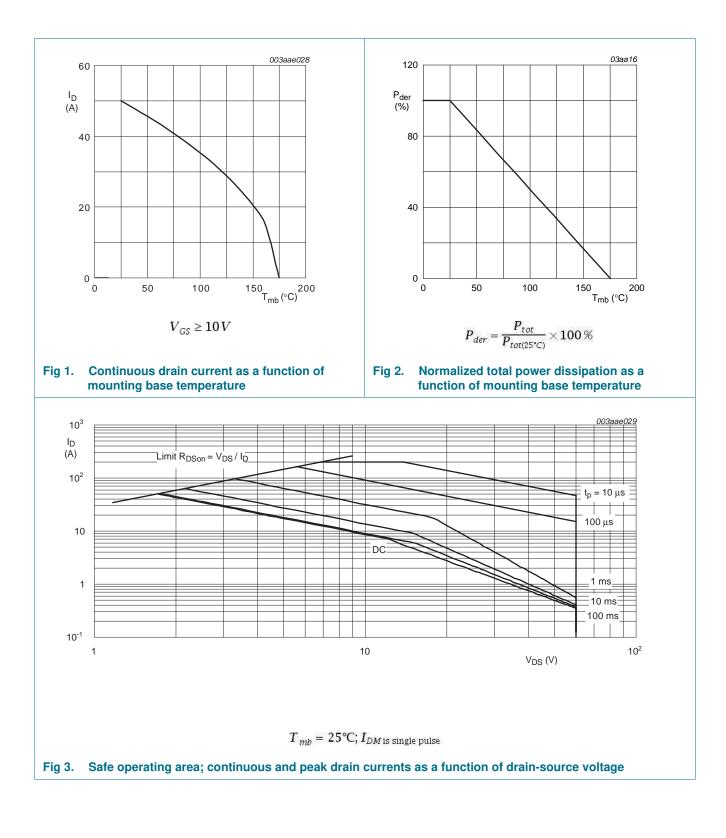
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Thermal characteristics 5.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	1	1.74	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	60	-	K/W

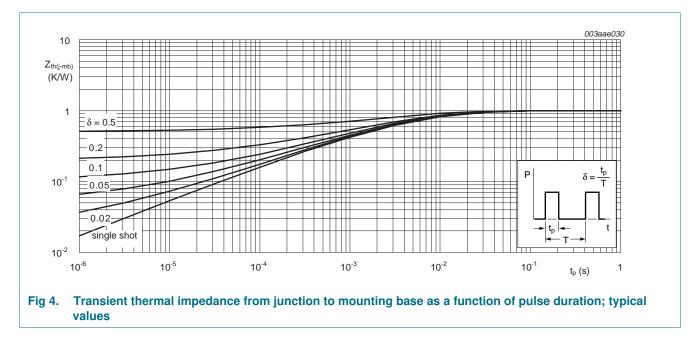


Table 5 Thermal characteristics

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6. Characteristics

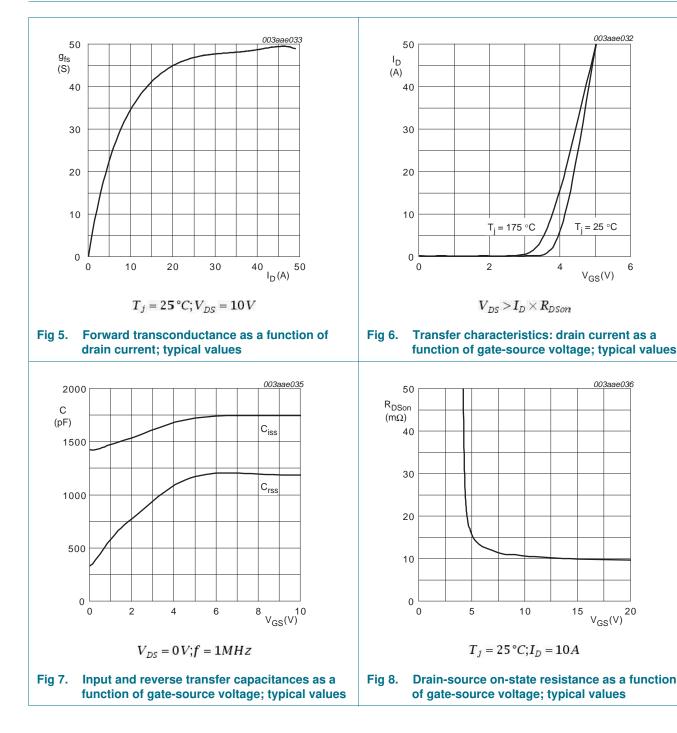
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	54	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
V _{GSth}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 11</u>	-	-	4.8	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	1	-	-	V	
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.03	2	μA
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	30	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	28.9	34	mΩ
	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; I_D = 15 \; A; T_j = 100 \; ^\circ C; \\ \text{see } \overline{Figure \; 12} \end{array}$	-	-	23.7	mΩ	
		V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; see <u>Figure 13</u>	-	12.6	14.8	mΩ
R _G	gate resistance	f = 1 MHz	-	1.3	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 30 V; V_{GS} = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	20.9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	17	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	6.2	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	I_D = 25 A; V_{DS} = 30 V; V_{GS} = 10 V; see Figure 14	-	3.7	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.4	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; \text{V}_{DS} = 30 \text{V}; \text{V}_{GS} = 10 \text{V};$ see Figure 14; see Figure 15	-	4.7	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 30 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	4.8	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1220	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	169	-	pF
C _{rss}	reverse transfer capacitance		-	95	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	13	-	ns
t _{d(off)}	turn-off delay time		-	27	-	ns
t _f	fall time		-	7	-	ns

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	Table 6.	Characteristics	continued
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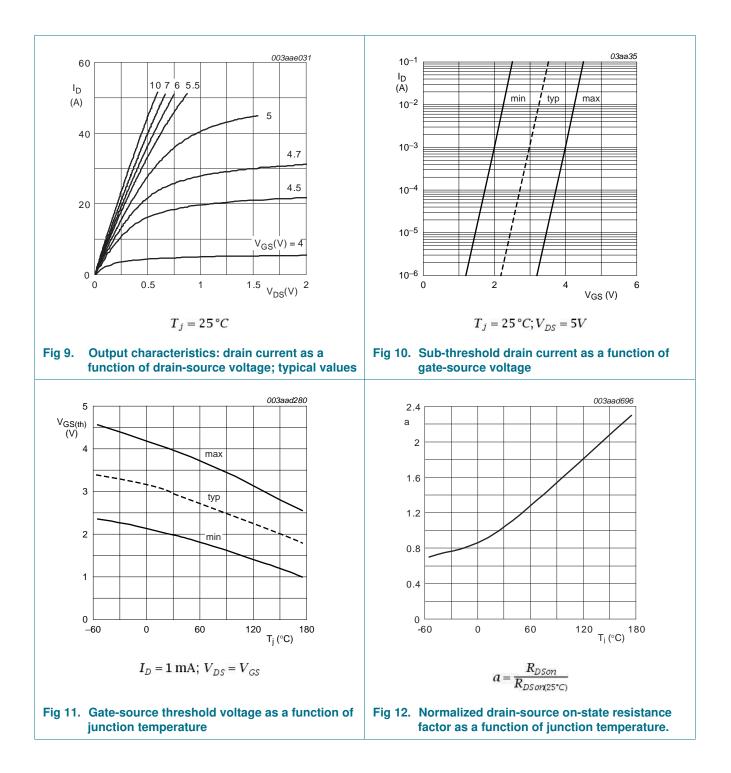
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
V _{SD}	source-drain voltage	$I_{S} = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s};$	-	31	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 30 V$	-	28.5	-	nC



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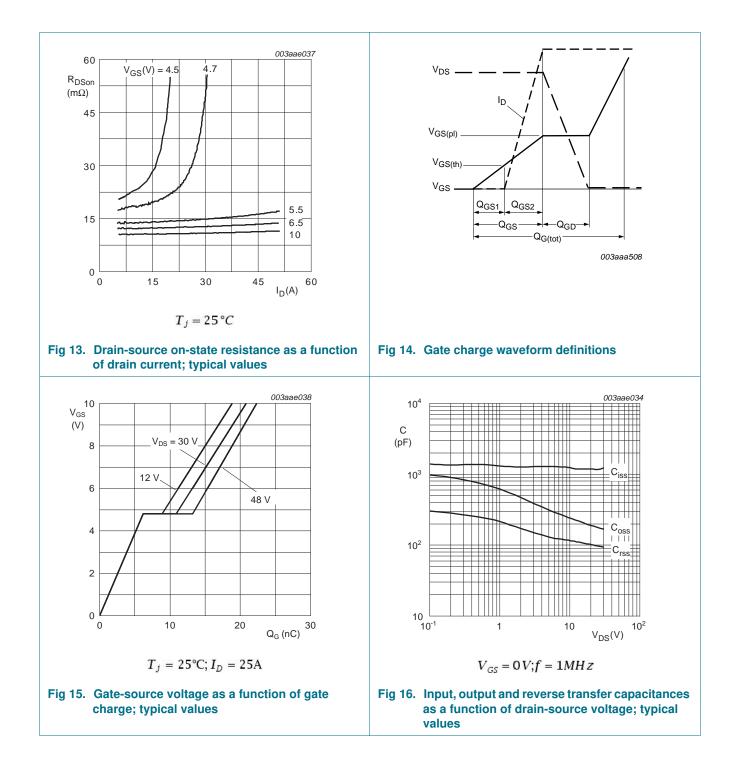
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7. Package outline

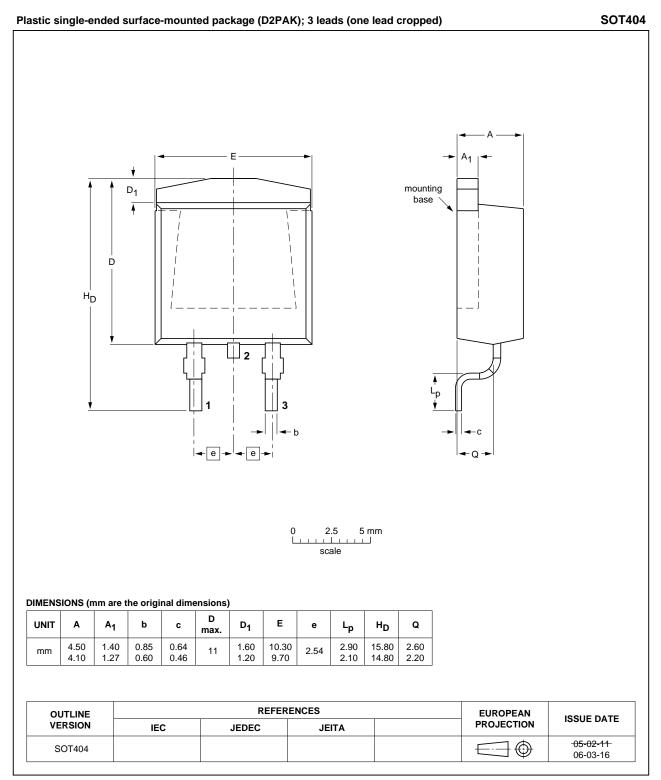


Fig 17. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision I	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN015-60BS v.2	20120301	Product data sheet	-	PSMN015-60BS v.1
Modifications:	Status changeVarious chang	d from objective to product. es to content.		
PSMN015-60BS v.1	20111021	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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